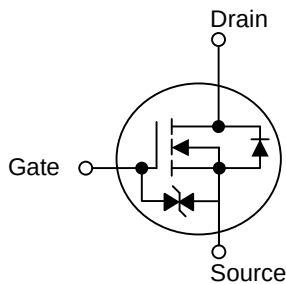
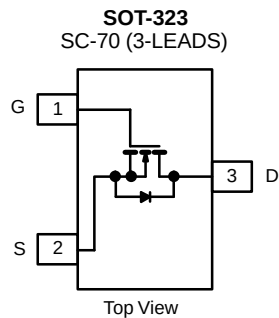


DMN62D0UWQ-7-VB Datasheet

N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (mA)
60	2 at $V_{GS} = 10$ V	300



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Low On-Resistance: 2 Ω
- Low Threshold: 2 V (typ.)
- Low Input Capacitance: 25 pF
- Fast Switching Speed: 25 ns
- Low Input and Output Leakage
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

APPLICATIONS

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$) ^b	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	300	mA
	$T_A = 100\text{ }^{\circ}\text{C}$		190	
Pulsed Drain Current ^a		I_{DM}	800	
Power Dissipation ^b	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	0.35	W
	$T_A = 100\text{ }^{\circ}\text{C}$		0.14	
Maximum Junction-to-Ambient ^b		R_{thJA}	350	$^{\circ}\text{C/W}$
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	$^{\circ}\text{C}$

Notes:

a. Pulse width limited by maximum junction temperature.

b. Surface Mounted on FR4 board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS T _A = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ. ^a	Max.	
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 10 μA	60			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		2.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 10	μA
		V _{DS} = 0 V, V _{GS} = ± 15 V			1	
		V _{DS} = 0 V, V _{GS} = ± 10 V			± 150	nA
		V _{DS} = 0 V, V _{GS} = ± 10 V, T _J = 85 °C			± 1000	
		V _{DS} = 0 V, V _{GS} = ± 5 V			± 100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 60 V, V _{GS} = 0 V , T _J = 125 °C			500	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V, V _{DS} = 7.5 V	800			mA
		V _{GS} = 4.5 V, V _{DS} = 10 V	500			
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 500 mA		2		Ω
		V _{GS} = 4.5 V, I _D = 200 mA		4		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 200 mA	100			mS
Diode Forward Voltage	V _{SD}	I _S = 200 mA, V _{GS} = 0 V			1.3	V
Dynamic ^a						
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V I _D ≅ 250 mA		0.4	0.6	nC
Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V f = 1 MHz		30		pF
Output Capacitance	C _{oss}			6		
Reverse Transfer Capacitance	C _{rss}			2.5		
Switching ^{a, b, c}						
Turn-On Time	t _{d(on)}	V _{DD} = 30 V, R _L = 150 Ω			25	ns
Turn-Off Time	t _{d(off)}	I _D ≅ 200 mA, V _{GEN} = 10 V, R _G = 10 Ω			35	

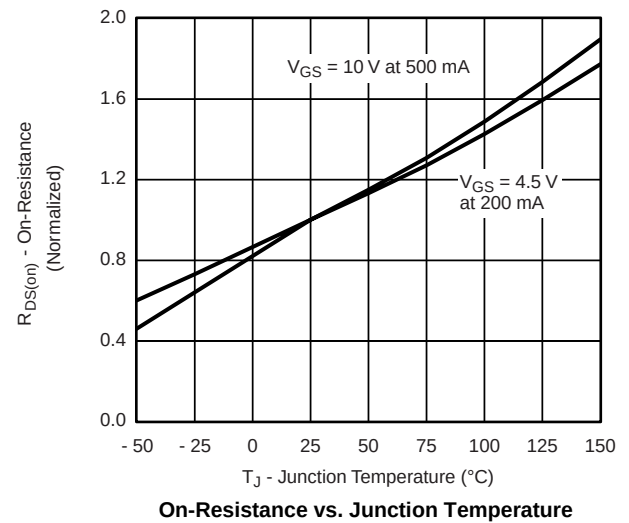
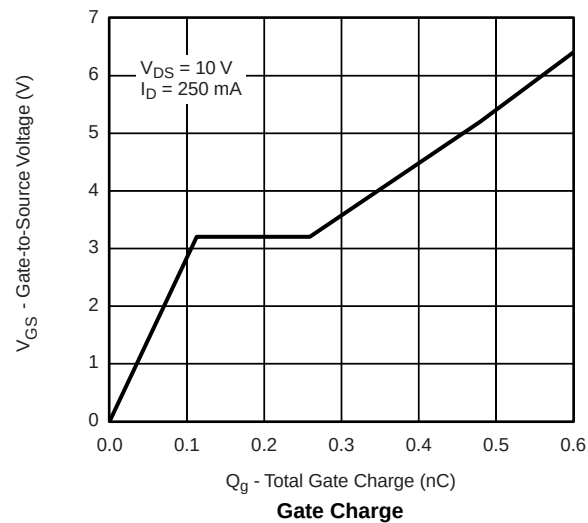
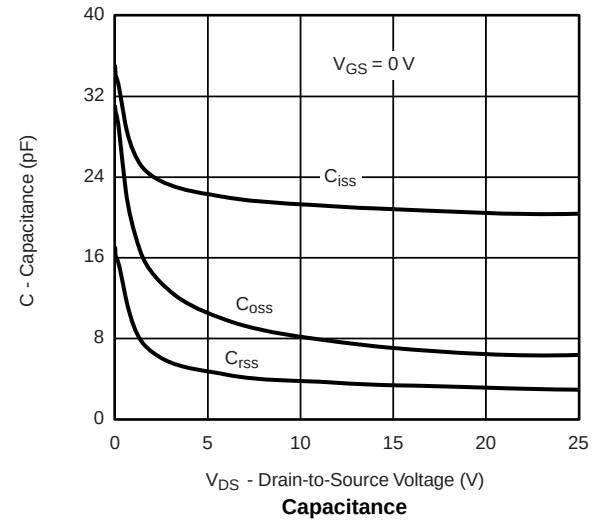
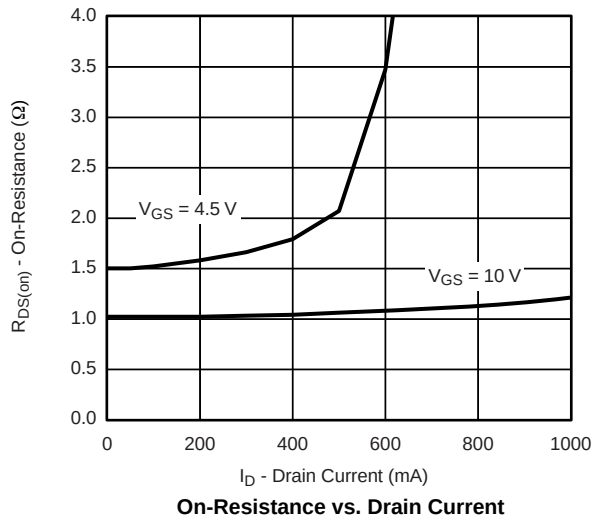
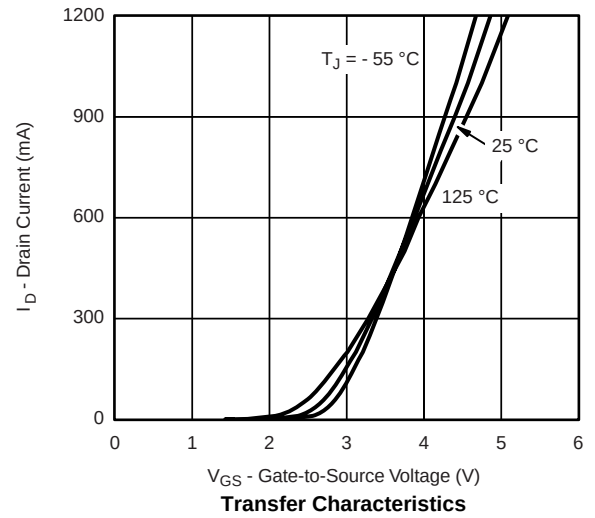
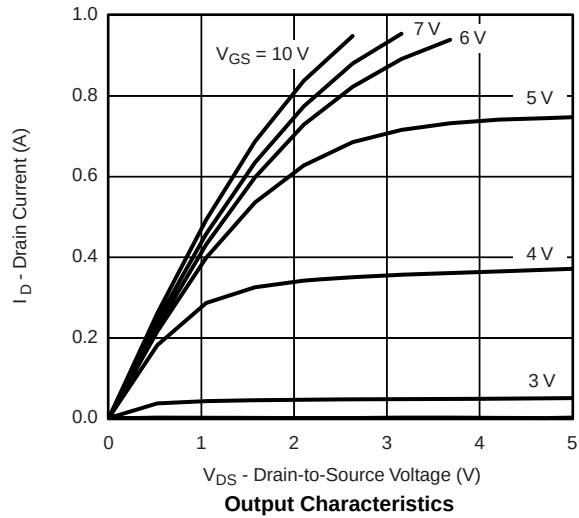
Notes:

a. For DESIGN AID ONLY, not subject to production testing.

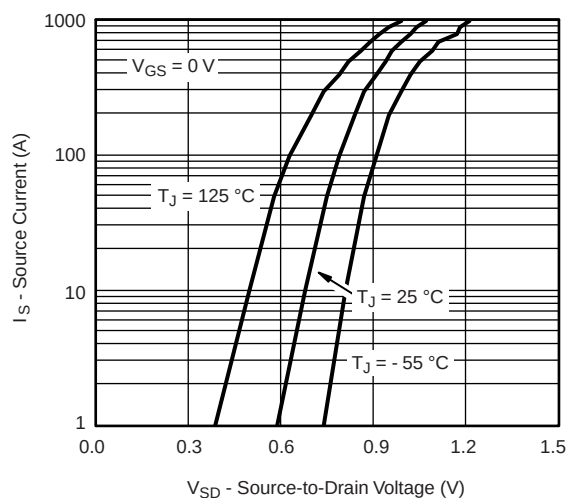
b. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.

c. Switching time is essentially independent of operating temperature.

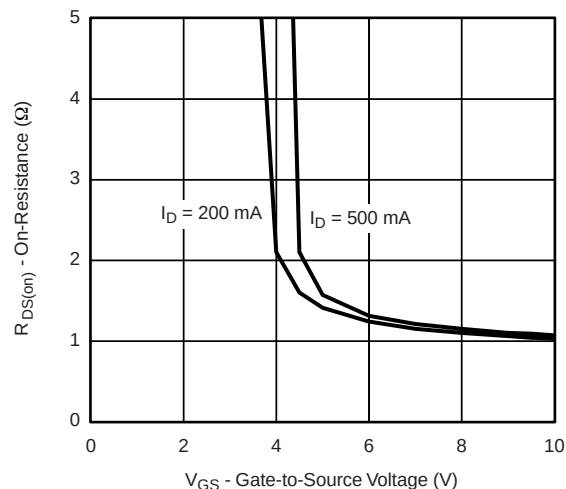
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


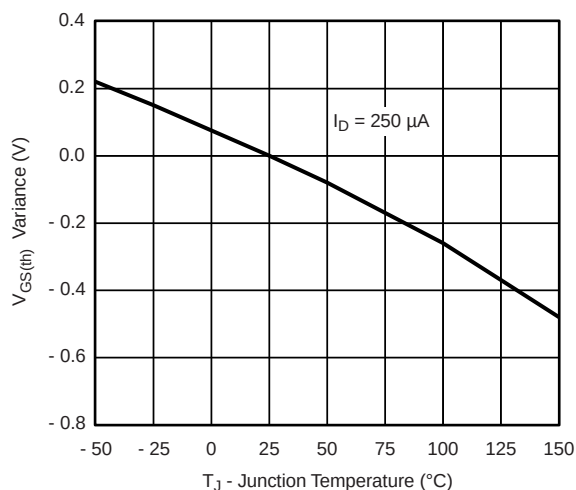
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



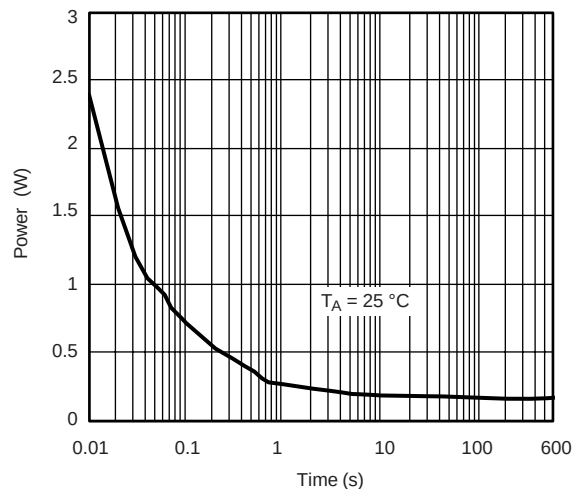
Source-Drain Diode Forward Voltage



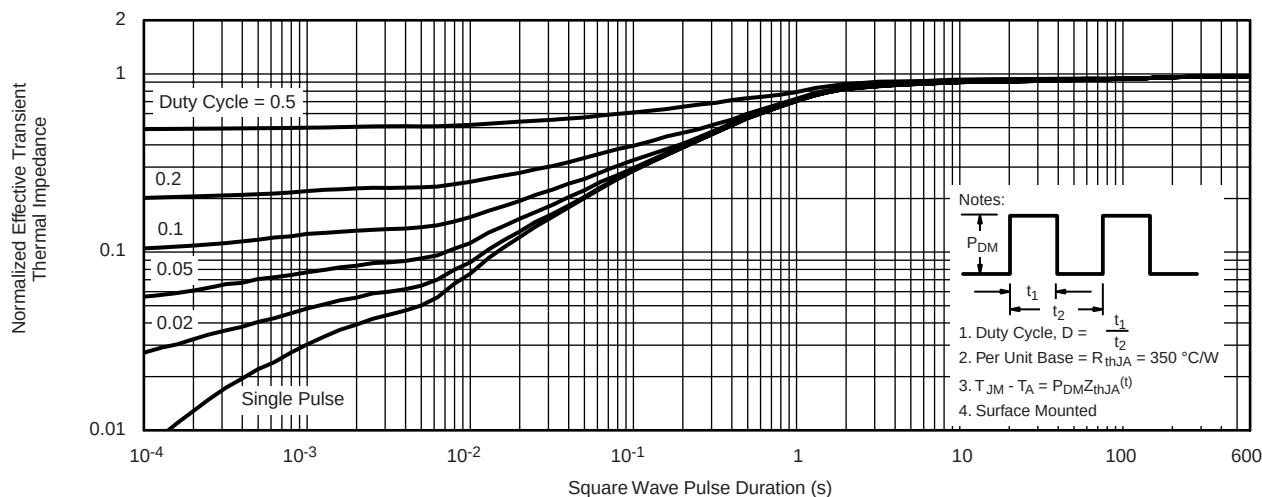
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature

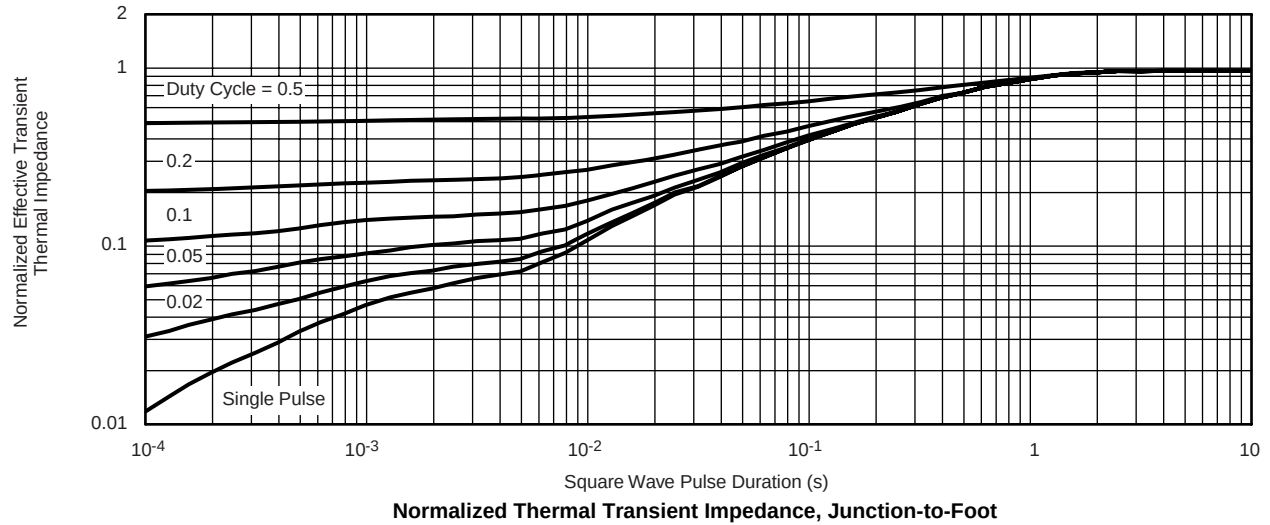


Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

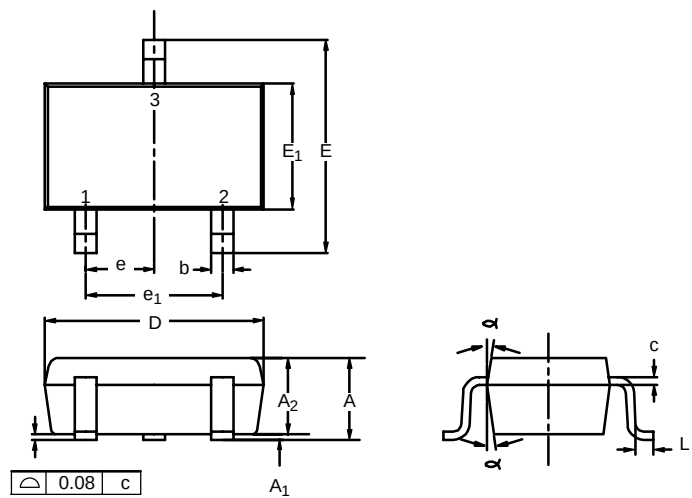
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

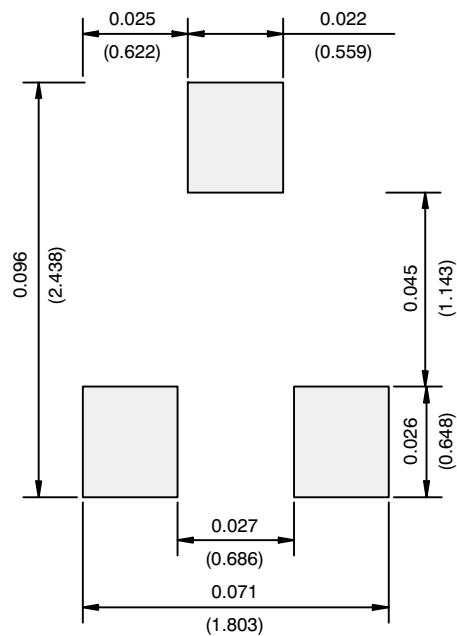
SC-70: 3-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	—	1.10	0.035	—	0.043
A ₁	—	—	0.10	—	—	0.004
A ₂	0.80	—	1.00	0.031	—	0.039
b	0.25	—	0.40	0.010	—	0.016
c	0.10	—	0.25	0.004	—	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		

ECN: S-03946—Rev. C, 09-Jul-01
DWG: 5549

RECOMMENDED MINIMUM PADS FOR SC-70: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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